

## / Descriptions

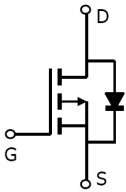
## / Features

$V_{DS} (V) = -16V$      $I_D = -12A$   
 $R_{DS(ON)}@-4.5V$  14m (Type.12.6m )  
 $R_{DS(ON)}@-2.5V$  25m (Type.17.0m )  
 $R_{DS(ON)}@-1.8V$  100m (Type.23.5m )  
HF Product.

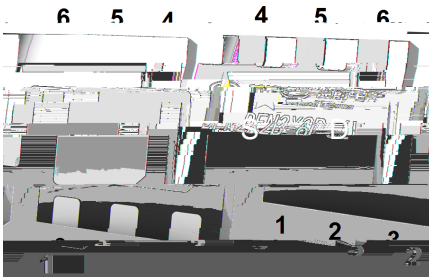
## / Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

## / Equivalent Circuit



## / Pinning



## / Marking

See Marking Instructions.

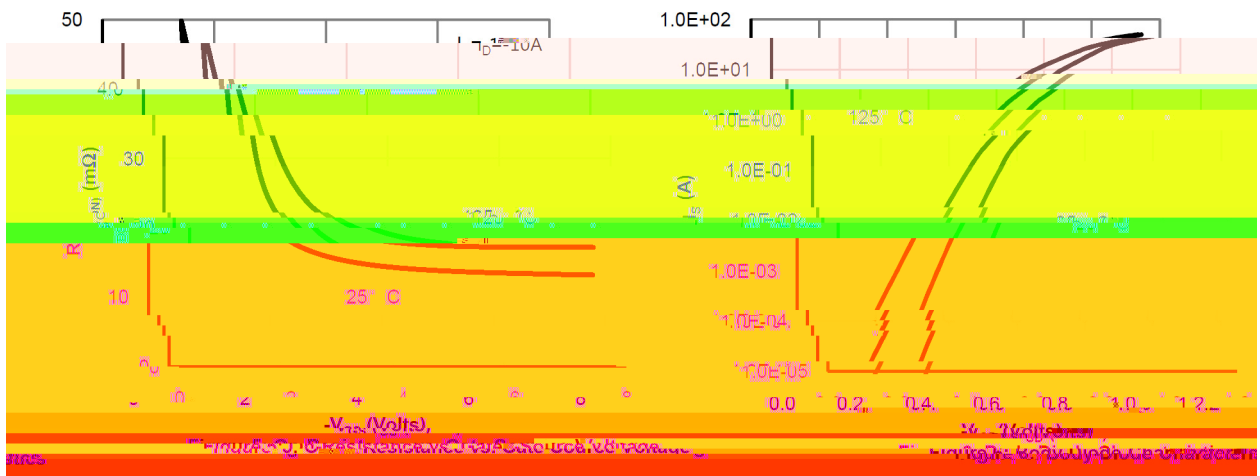
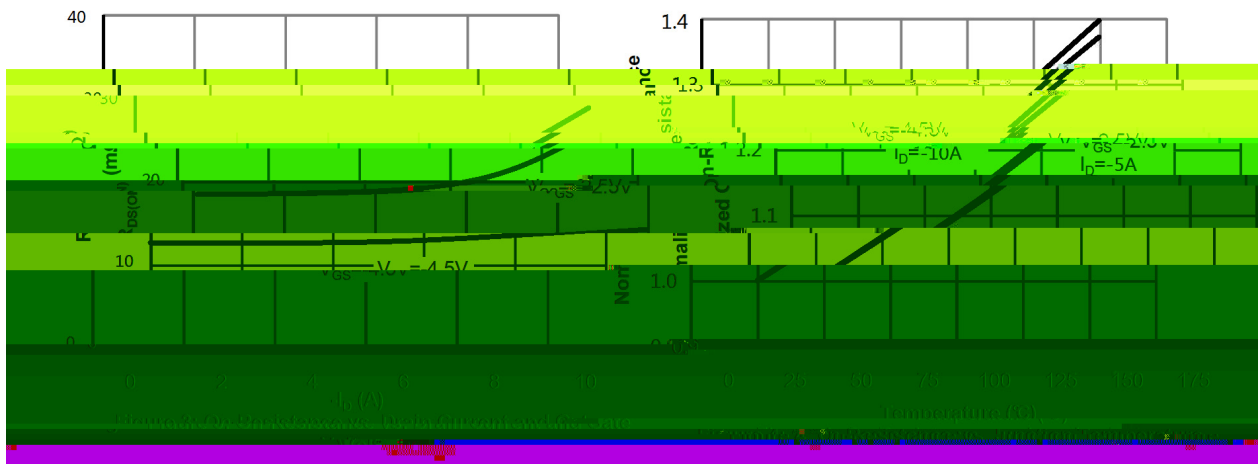
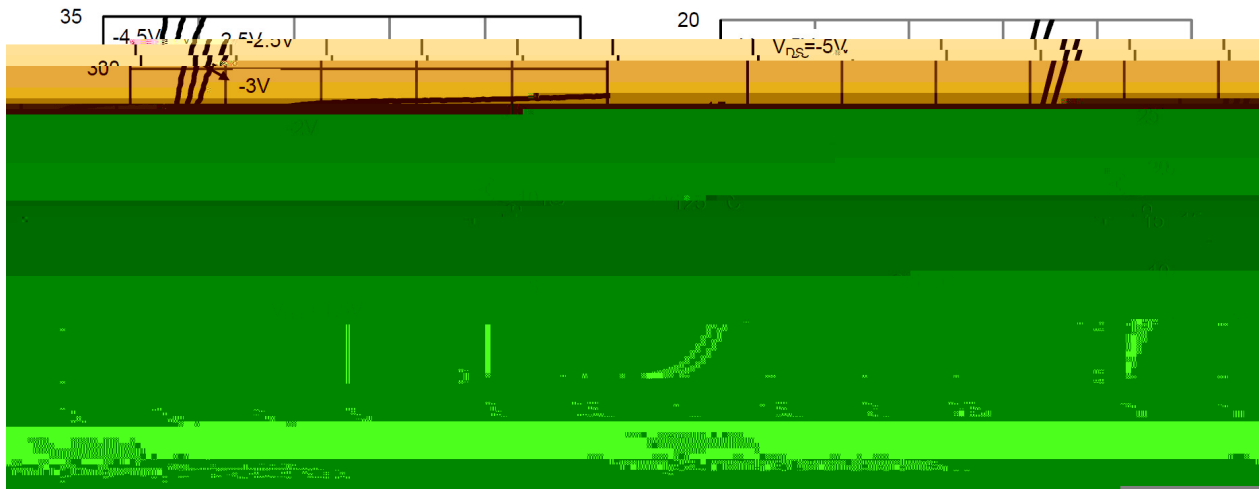
## / Absolute Maximum Ratings(Ta=25 )

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-16	V
Gate-Source Voltage	V <sub>GSS</sub>	±10	V
Continuous Drain Current	I <sub>D</sub>	-12	A
Pulsed Drain Current	I <sub>DM</sub>	-42	A
Power Dissipation for Single Operation	P <sub>D</sub>	3.0	W
Maximum Junction Temperature	T <sub>j</sub>	150	
Storage Temperature Range	T <sub>stg</sub>	-55 150	
Thermal Resistance-Junction to Ambient	R <sub>JA</sub>	41.7	/W

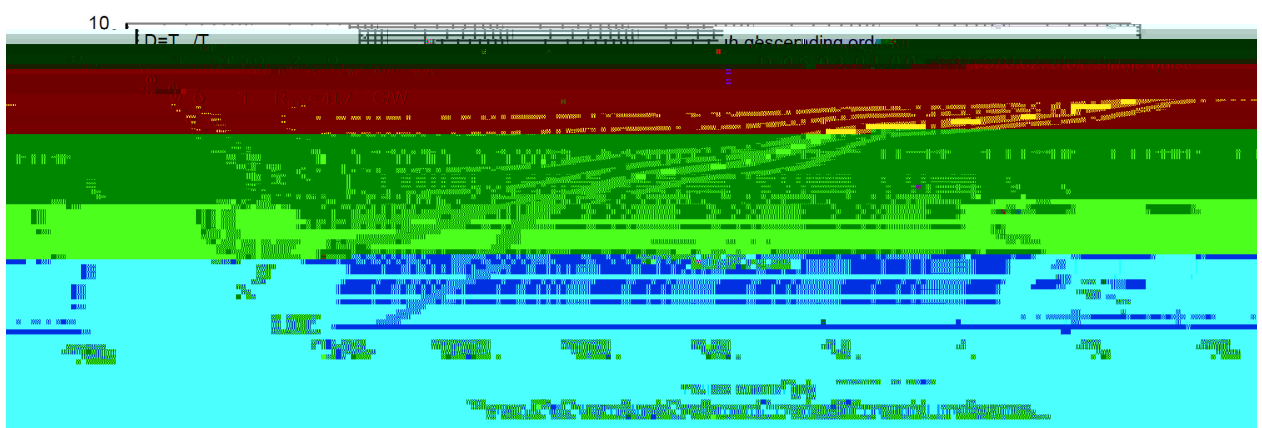
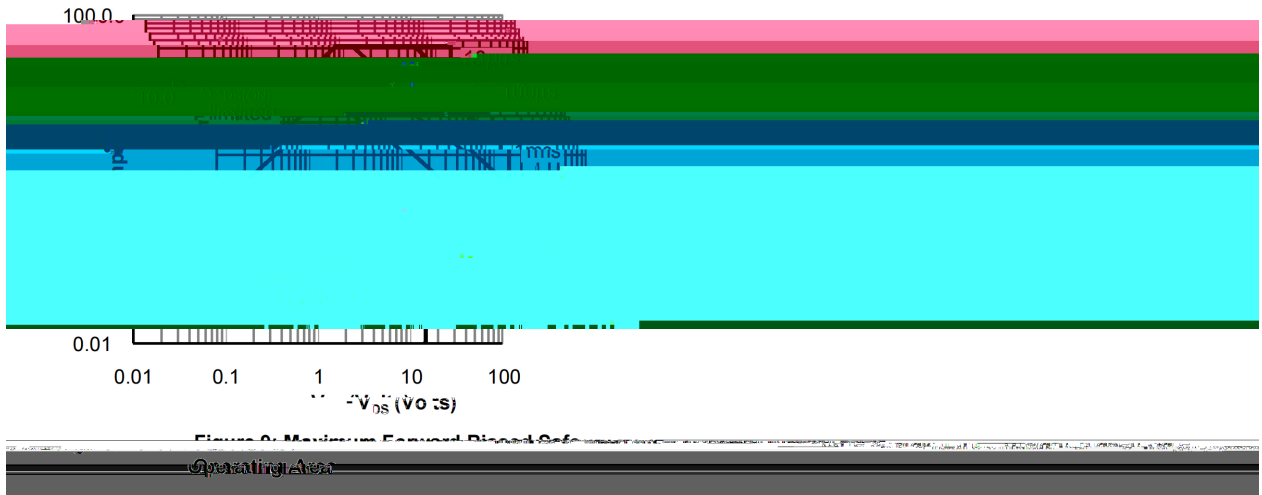
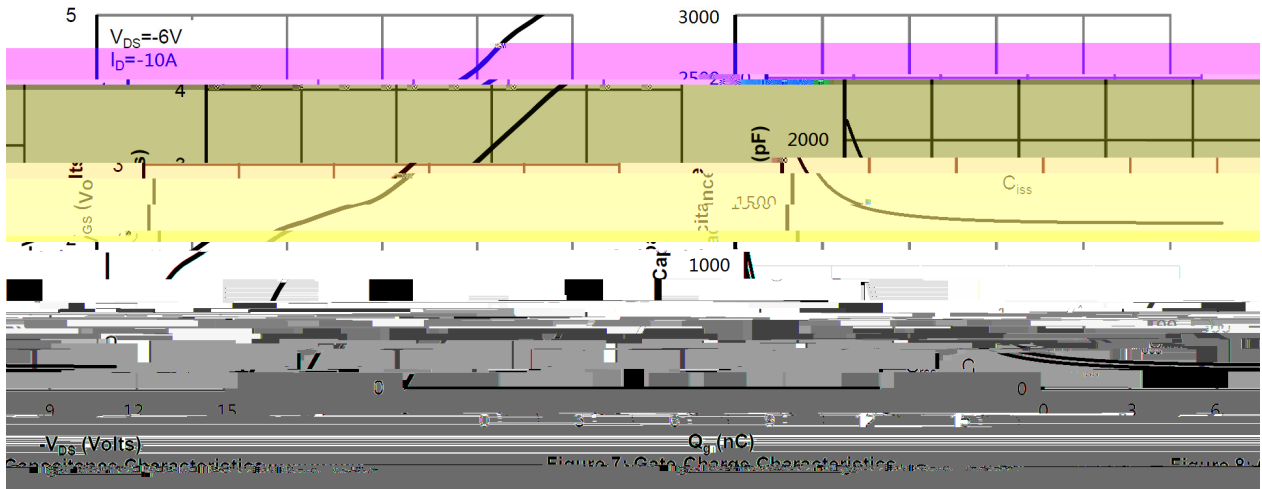
## / Electrical Characteristics(Ta=25 )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =-250μA V <sub>GS</sub> =0V	-16	-19		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-16V V <sub>GS</sub> =0V			-1.0	μA
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V V <sub>GS</sub> =±10V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	-0.3	-0.7	-1.5	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V I <sub>D</sub> =-10A		12.6	14	m
		V <sub>GS</sub> =-2.5V I <sub>D</sub> =-5A		17.0	25	
		V <sub>GS</sub> =-1.8V I <sub>D</sub> =-5A		23.5	100	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A V <sub>GS</sub> =0V			-1.2	V
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		10.3		
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V V <sub>DS</sub> =-8V f=1MHz		1365		pF
Output Capacitance	C <sub>oss</sub>			220		
Reverse Transfer Capacitance	C <sub>rss</sub>			180		
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-4.5V V <sub>DS</sub> =-10V I <sub>D</sub> =-8A		14.1		nC
Gate-Source Charge	Q <sub>gs</sub>			1.3		
Gate-Drain Charge	Q <sub>gd</sub>			3.1		
Turn-on Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> =-4.5V V <sub>DS</sub> =-10V I <sub>D</sub> =-8A R <sub>g</sub> =3		12.2		ns
Turn-on Rise Time	t <sub>r</sub>			60.6		
Turn-off Delay Time	t <sub>d(OFF)</sub>			68.6		
Turn-off Fall Time	t <sub>f</sub>			41.7		

/ Electrical Characteristic Curve



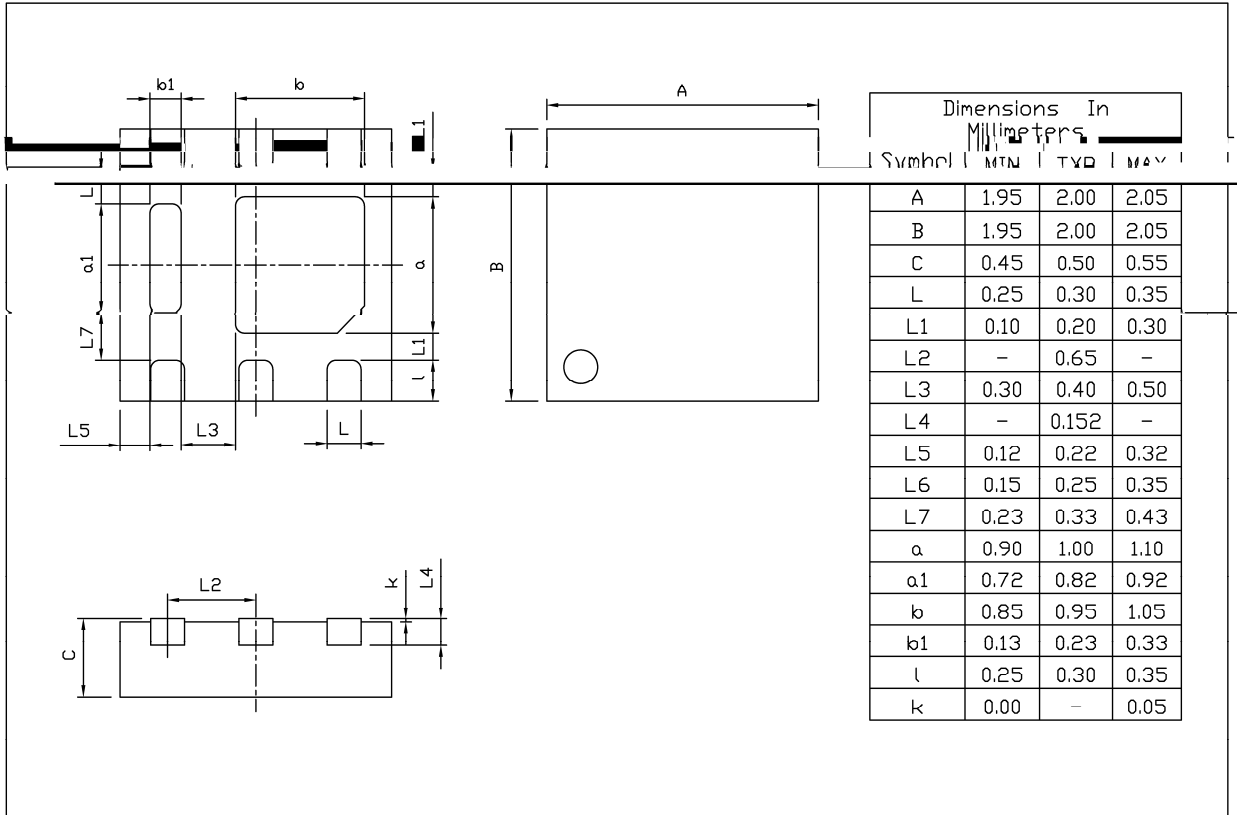
/ Electrical Characteristic Curve



**/ Package Dimensions**

DFN2 X2B-6L-0.5

Unit:mm



Rev.01 202006

/ Marking Instructions



BR

130P016

\*\*\*\*

Note:

BR: Company Code

130P016: Product Type Code

\*\*\*\*: Lot No. Code, code change with Lot No

**( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)**



Note:

- |   |     |     |    |          |   |
|---|-----|-----|----|----------|---|
| 1 | 150 | 180 | 60 | 90sec;   | 1.Preheating:150~180 , Time:60~90sec.   |
| 2 | 245 | 5   | 5  | 0.5sec;  | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 |     |     | 2  | 10 /sec. | 3. Cooling Speed: 2~10 /sec.            |

**/ Resistance to Soldering Heat Test Conditions**

260 5                      10 1 sec.                      Temp.:260±5                      Time:10±1 sec

**/ Packaging SPEC.**

/ REEL

Package Type	Units					Dimension (unit mm <sup>3</sup> )		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
DFN2x2B-6L	4,000	10	40,000	4	160,000	7 x8	210x205x205	445x435x230

**/ Notices**

All information provided in this document is subject to legal disclaimers.